

SN UNKNOWN

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

| | | | |
|---|--|-----------------|------------|
| Applicant: | Leonard Forbes et al. | Examiner: | |
| Serial No.: | Unknown | Group Art Unit: | 2811 |
| Filed: | Herewith | Docket: | 303.523US2 |
| Title: | ANTIFUSE STRUCTURES, METHODS, AND APPLICATIONS | | |
| (Continuation of U.S. Serial No. 09/258,363, filed February 26, 1999) | | | |

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Prior to examination, please amend the above-identified continuation application as follows.

In the Specification

On page 1, after the title, please add the following section:

--Related Application

This is a continuation of U.S. Patent Application Serial No. 09/258,363, filed February 26, 1999, which application is incorporated herein by reference.--

In the Claims

Please substitute the claim set in the appendix entitled Clean Version of Pending Claims for the previously pending claim set. The substitute claim set is intended to reflect amendment of original claims 52 and 60, and addition of new claims 72-94. The specific amendments to individual claims are detailed in the following marked up claims:

52. (Amended) A method of making an antifuse in an integrated-circuit assembly, the method comprising:

[a step for] forming an opening in an insulative layer, with the opening exposing one or more conductors;

[a step for] forming a metal layer in the opening;

[a step for] forming a metal-oxide layer on the metal layer and within the opening,

[a step for] forming a conductive layer on the metal-oxide layer and within the opening;

and

[a step for] forming at least one conductive member on the insulative layer which

PRELIMINARY AMENDMENT

Serial Number: 09/258,363

Filing Date: February 26, 1999

Title: ANTIFUSE STRUCTURES, METHODS, AND APPLICATIONS

Page 2

Dkt: 303.523US1

overhangs the opening.

60. (Amended) A method of making an antifuse in an integrated-circuit assembly, the method comprising:

[a step for] forming an opening in an insulative layer, with the opening exposing at least one conductor;

[a step for] forming a metal layer in the opening;

[a step for] forming a metal-oxide layer on the metal layer and within the opening,

[a step for] forming a conductive layer on the metal-oxide layer and within the opening;

[a step for] forming at least one conductive member on the insulative layer which overhangs the opening; and

[a step for] at least partially saturating the metal layer with a gas comprising more than trace quantities of hydrogen or nitrogen.

Remarks

The specification has been amended to add priority information.

Claims 52 and 60 have been amended, and claims 72-94 have been added. Claims 1-94 are pending in this application.

Respectfully submitted,

LEONARD FORBES ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938
Minneapolis, MN 55402
(612) 349-9593

Date

30 Aug 2001

By

Eduardo E. Drake
Reg. No. 40,594

"Express Mail" mailing label number: EL 671640564 US

Date of Deposit: August 30, 2001

This paper or fee is being deposited on the date indicated above with the United States Postal Service pursuant to 37 CFR 1.10, and is addressed to the Commissioner for Patents, Box Patent Application, Washington, D.C. 20231.

APPENDIX: CLEAN VERSION OF PENDING CLAIMS

1. An antifuse structure in an integrated circuit, comprising:
first and second noncontacting conductive members; and
means for moving the second conductive member relative the first conductive member.
2. The antifuse structure of claim 1, wherein the means for moving the second conductive member comprises a material composition including a gas in solid solution.
3. The antifuse structure of claim 1, wherein the means for moving the second conductive member comprises a material composition including hydrogen in solid solution or in a hydride phase.
4. The antifuse structure of claim 1, wherein the means for moving the second conductive member comprises at least one of titanium, hafnium, niobium, tantalum, thorium, vanadium, and zirconium, and hydrogen in solid solution or in a hydride phase.
5. The antifuse structure of claim 1, wherein the means for moving the second conductive member comprises a thin-film resistor and a layer comprising at least one of the following compounds: Pb_3O_4 , PbO_2 , HgO , Ag_2O , MnO_2 , Ag_2O , K_3N , Rb_3N , $\text{ReN}_{0.43}$, Co_3N , Ni_3N , or Cd_3N_2 .
6. An antifuse structure in an integrated circuit, comprising:
first and second noncontacting conductive members; and
a layer comprising a gas in solid solution or a hydride phase adjacent to one of the first and second noncontacting conductive members.
7. The antifuse structure of claim 6, wherein the layer comprises a material composition including hydrogen in solid solution or in a hydride phase.
8. The antifuse structure of claim 6, wherein the layer comprises at least one of titanium, hafnium, niobium, tantalum, thorium, vanadium, and zirconium, and hydrogen in solid solution

or in a hydride phase.

9. The antifuse structure of claim 6, wherein the first noncontacting conductive member lies at least partly between the layer comprising the gas in solid solution or hydride phase and the second noncontacting conductive member.

10. An antifuse structure in an integrated circuit, comprising:
first and second noncontacting conductive members; and
a layer comprising a gas in solid solution or hydride phase for moving the second
conductive member relative the first conductive member.

11. The antifuse structure of claim 10, wherein the layer comprises a material composition including hydrogen in solid solution or in a hydride phase.

12. The antifuse structure of claim 10, wherein the layer comprises at least one of titanium, hafnium, niobium, tantalum, thorium, vanadium, and zirconium, and hydrogen in solid solution or in a hydride phase.

13. The antifuse structure of claim 10, wherein the first noncontacting conductive member lies at least partly between the layer comprising the gas in solid solution or hydride phase and the second noncontacting conductive member.

14. An antifuse structure in an integrated circuit, comprising:
first and second noncontacting conductive members; and
a layer adjacent to one of the first and second noncontacting conductive members and
comprising at least one of titanium, hafnium, niobium, tantalum, thorium,
vanadium, and zirconium, and hydrogen in solid solution or in a hydride phase.

15. An antifuse structure in an integrated circuit, comprising:
first and second noncontacting conductive members; and

09/258,363

a layer adjacent to one of the first and second noncontacting conductive members and comprising at least one of a metal hydride, Pb_3O_4 , PbO_2 , HgO , Ag_2O , MnO_2 , Ag_2O , K_3N , Rb_3N , $ReN_{0.43}$, Co_3N , Ni_3N , or Cd_3N_2 or a compound which can be charged with hydrogen, oxygen or nitrogen to yield one of these compounds.

16. An antifuse structure in an integrated circuit, comprising:
first and second noncontacting conductive members; and
a layer adjacent to the second noncontacting conductive members for moving the second conductive member into contact with the first conductive member, the layer comprising at least one of titanium, hafnium, niobium, tantalum, thorium, vanadium, and zirconium, and hydrogen in solid solution or in a hydride phase.
17. An antifuse structure in an integrated circuit, comprising:
a chamber having a bottom and a top and one or more interior walls extending between the top and bottom;
a high-gas-saturatable layer at least partially within the chamber; and
a conductive, low-gas-saturatable layer between the high-gas-saturatable layer and the top of the chamber.
18. The antifuse structure of claim 17 wherein the high-gas-saturatable layer has a hydrogen-gas-solubility at least 10 times greater than that of the conductive, low-gas-saturatable layer.
19. The antifuse structure of claim 17, wherein the chamber comprises:
a substrate; and
an insulative layer on the substrate and having an opening exposing a portion of the substrate, with the exposed portion of the substrate defining at least a portion of the bottom of the chamber and the opening defining the interior sidewalls of the chamber.
20. An antifuse structure in an integrated circuit, comprising:

a chamber having a bottom and a top and one or more interior walls extending between the top and bottom;
a high-gas-saturatable layer at least partially within the chamber;
a conductive, low-gas-saturatable layer between the high-gas-saturatable layer and the top of the chamber; and
first and second conductive members overhanging the top of the chamber.

21. The antifuse structure of claim 20 wherein the high-gas-saturatable layer has a hydrogen-gas-solubility at least five times greater than that of the conductive, low-gas-saturatable layer.

22. The antifuse structure of claim 20, wherein the high-gas-saturatable layer comprises at least one of titanium, hafnium, niobium, tantalum, thorium, vanadium, and zirconium.

23. The antifuse structure of claim 20 wherein the chamber comprises:
a substrate; and
an insulative layer on the substrate and having an opening exposing a portion of the substrate, with the exposed portion of the substrate defining at least a portion of the bottom of the chamber and the opening defining the interior sidewalls of the chamber.

24. An antifuse structure in an integrated circuit, comprising:
a chamber having a bottom and a top and one or more interior walls extending between the top and bottom;
a conductive layer within the chamber;
a layer within the chamber between the conductive layer and the bottom of the chamber, and comprising a material having a hydrogen-gas-solubility at least 10 times greater than that of at least a portion of the conductive layer; and
first and second conductive members overhanging the top of the chamber.

25. The antifuse structure of claim 24 wherein the chamber comprises:

a substrate; and

an insulative layer on the substrate and having an opening exposing a portion of the substrate, with the exposed portion of the substrate defining at least a portion of the bottom of the chamber and the opening defining the interior sidewalls of the chamber.

26. The antifuse structure of claim 24 wherein the first and second conductive members overhang the chamber by at least 250 angstroms.

27. The antifuse structure of claim 24, wherein the layer comprises at least one of titanium, hafnium, niobium, tantalum, thorium, vanadium, and zirconium, and hydrogen in solid solution or hydride phases.

28. The antifuse structure of claim 24, wherein the layer within the chamber comprises Pb_3O_4 , PbO_2 , HgO , Ag_2O , MnO_2 , Ag_2O , K_3N , Rb_3N , $\text{ReN}_{0.43}$, Co_3N , Ni_3N , or Cd_3N_2 .

29. The antifuse structure of claim 24, wherein the conductive layer comprises at least one of aluminum, copper, silver, and gold.

30. An antifuse structure in an integrated circuit, comprising:

a chamber having a bottom and a top and one or more interior walls extending between the top and bottom;

a conductive layer within the chamber and comprising at least one of aluminum, copper, silver, and gold;

a layer lying within the chamber between the conductive layer and the bottom of the chamber, and comprising at least one of titanium, hafnium, niobium, tantalum, thorium, vanadium, and zirconium, and hydrogen in solid solution or in one or more hydride phases or at least one of Pb_3O_4 , PbO_2 , HgO , Ag_2O , MnO_2 , Ag_2O , K_3N , Rb_3N , $\text{ReN}_{0.43}$, Co_3N , Ni_3N , or Cd_3N_2 ; and

first and second conductive members each overhanging the top of the chamber by at least

250 angstroms.

31. The antifuse structure of claim 30 wherein the chamber comprises:
a substrate; and
an insulative layer on the substrate and having an opening exposing a portion of the
substrate, with the exposed portion of the substrate defining at least a portion of
the bottom of the chamber and the opening defining the interior sidewalls of the
chamber.
32. An antifuse structure in an integrated circuit, comprising:
a chamber having a bottom and a top and one or more interior walls extending between
the top and bottom;
a conductive layer within the chamber and comprising at least one of aluminum, copper,
silver, and gold; and
first and second conductive members each overhanging the top of the chamber by at least
250 angstroms.
33. The antifuse structure of claim 32 wherein the chamber comprises:
a substrate; and
an insulative layer on the substrate and having an opening exposing a portion of the
substrate, with the exposed portion of the substrate defining at least a portion of
the bottom of the chamber and the opening defining the interior sidewalls of the
chamber.
34. An antifuse structure in an integrated circuit, comprising:
a chamber having a bottom and a top and one or more interior walls extending between
the top and bottom;
a conductive layer within the chamber and comprising at least one of aluminum, copper,
silver, and gold; and
first and second conductive members each overhanging the top of the chamber by at least

FOIEB0 "T6454650

250 angstroms and contacting the conductive layer within the chamber.

35. The antifuse structure of claim 34 wherein the first and second conductive members are fused to the conductive layer.
36. A structure for a programmable electrical connection in an integrated circuit, comprising:
a chamber having a bottom and a top and one or more interior walls extending between the top and bottom;
a conductive layer within the chamber; and
one or more conductive members, each overhanging the top of the chamber.
37. A programmable electrical connection comprising:
a layer having a cavity;
first and second conductive members having respective first and second ends overhanging the cavity;
a third conductive member in the cavity spaced from the first and second ends; and
means for displacing the third conductive member toward the first and second ends of the first and second conductive members.
38. The programmable electrical connection of claim 37 wherein the means for displacing the third conductive member toward the first and second ends includes a layer comprising a gas in solid solution or in a hydride phase or a layer comprising at least one of the following compounds: Pb_3O_4 , PbO_2 , HgO , Ag_2O , MnO_2 , Ag_2O , K_3N , Rb_3N , $\text{ReN}_{0.43}$, Co_3N , Ni_3N , or Cd_3N_2 .
39. A structure for a programmable electrical connection in an integrated circuit, comprising:
first and second conductive members; and
means for moving the second conductive member relative the first conductive member.
40. An integrated circuit comprising:
one or more transistors; and

one or more programmable electrical connections integral to the circuit and coupled to each of the one or more transistors, with each programmable electrical connection comprising:
at least a first and a second conductive member; and
means for moving the second conductive member relative the first conductive member.

41. The integrated circuit of claim 40, wherein the means for moving the second conductive member relative the first conductive member moves the second conductive member toward the first conductive member.

42. An integrated circuit comprising:
one or more transistors; and
one or more programmable electrical connections, with each coupled to at least one of the one or more transistors and comprising:
at least a first and a second conductive member; and
means for moving the second conductive member relative the first conductive member.

43. The integrated circuit of claim 42, wherein the means for moving the second conductive member relative the first conductive member moves the second conductive member toward the first conductive member.

44. A programmable logic array comprising:
one or more transistors; and
one or more programmable electrical connections coupled to each of the one or more transistors, with each programmable electrical connection comprising:
first and second conductive members; and
means for moving the second conductive member relative the first conductive member.

FILED FOR 09/258,363

45. The integrated circuit of claim 44, wherein the means for moving the second conductive member relative the first conductive member moves the second conductive member toward the first conductive member.

46. An integrated memory circuit comprising:
one or more memory cells;
one or more redundant memory cells; and
one or more programmable electrical connections coupled to each of the one or more redundant memory cells, with each programmable electrical connection comprising:
first and second conductive members; and
means for moving the second conductive member relative the first conductive member.

47. A system comprising:
a processor; and
an integrated circuit, with the integrated circuit including one or more programmable electrical connections coupled to each of the one or more redundant memory cells, with each programmable electrical connection comprising:
first and second conductive members; and
means for moving the second conductive member relative the first conductive member.

48. A method of making an antifuse in an integrated-circuit assembly, the method comprising:

forming an opening in an insulative layer;
forming a metal layer in the opening;
forming a metal-oxide layer on the metal layer,
forming a conductive layer on the metal-oxide layer; and
forming at least one conductive member on the insulative layer which overhangs the

opening.

49. The method of claim 48, wherein the metal layer in the opening comprises at least one of titanium, hafnium, niobium, tantalum, thorium, vanadium, and zirconium.

50. The method of claim 48, wherein the conductive layer comprises at least one of aluminum, gold, silver, and copper.

51. The method of claim 48, wherein the conductive member on the insulative layer overhangs the opening by at least 250 angstroms.

52. (Once Amended) A method of making an antifuse in an integrated-circuit assembly, the method comprising:

forming an opening in an insulative layer, with the opening exposing one or more conductors;

forming a metal layer in the opening;

forming a metal-oxide layer on the metal layer and within the opening,

forming a conductive layer on the metal-oxide layer and within the opening; and

forming at least one conductive member on the insulative layer which overhangs the opening.

53. The method of claim 52, wherein the metal layer in the opening comprises at least one of titanium, hafnium, niobium, tantalum, thorium, vanadium, and zirconium.

54. The method of claim 52, wherein the conductive layer comprises at least one of aluminum, gold, silver, and copper.

55. The method of claim 52, wherein the conductive member on the insulative layer overhangs the opening by at least 250 angstroms.

56. A method of making an antifuse in an integrated-circuit assembly, the method comprising:
- forming an opening in an insulative layer;
 - forming a metal layer in the opening;
 - forming a metal-oxide layer on the metal layer,
 - forming a conductive layer on the metal-oxide layer;
 - forming at least one conductive member on the insulative layer which overhangs the opening; and
 - at least partially saturating the metal layer with a gas.
57. The method of claim 56, wherein the metal layer in the opening comprises at least one of titanium, hafnium, niobium, tantalum, thorium, vanadium, and zirconium.
58. The method of claim 56, wherein the conductive layer comprises at least one of aluminum, gold, silver, and copper.
59. The method of claim 56, wherein the conductive member on the insulative layer overhangs the opening by at least 250 angstroms.
60. (Amended) A method of making an antifuse in an integrated-circuit assembly, the method comprising:
- forming an opening in an insulative layer, with the opening exposing at least one conductor;
 - forming a metal layer in the opening;
 - forming a metal-oxide layer on the metal layer and within the opening,
 - forming a conductive layer on the metal-oxide layer and within the opening;
 - forming at least one conductive member on the insulative layer which overhangs the opening; and
 - at least partially saturating the metal layer with a gas comprising more than trace quantities of hydrogen or nitrogen.

61. A method of operating an antifuse in an integrated circuit, the method comprising:
at least partially saturating a portion of the antifuse with a gas; and
releasing gas from the saturated portion of the antifuse to program the antifuse.
62. A method of operating an antifuse in an integrated circuit, the method comprising:
a step for at least partially saturating a portion of the antifuse with a gas; and
a step for releasing gas from the saturated portion of the antifuse to program the antifuse.
63. A method of operating an antifuse in an integrated circuit, the method comprising:
at least partially saturating a first member of the antifuse with a gas; and
releasing gas from the first member; and
in response to releasing gas from the first member, moving a second member into contact
with a third member.
64. The method of claim 63, wherein releasing gas from the first member comprises heating
at least the first member.
65. A method of operating an antifuse in an integrated circuit, the method comprising:
a step for at least partially saturating a first part of the antifuse with a gas;
a step for releasing gas from the first member; and
a step for moving a second member into contact with a third member, in response to the
step for releasing the gas.
66. A method of operating one or more antifuses in an integrated circuit, with each antifuse
having a normally open electrical connection, the method comprising:
at least partially saturating a portion of one or more of the antifuses with a gas;
releasing gas from the saturated portions of one or more of the antifuses; and
in response to releasing gas from the saturated portions of the one or more of the
antifuses, closing the normally open electrical connection of the one or more of
the antifuses.

67. The method of claim 66, wherein at least partially saturating a portion of one or more of the antifuses with a gas comprises at least partially saturating a layer with hydrogen.
68. The method of claim 66, wherein releasing gas from the saturated portion of the one or more antifuses comprises heating the saturated portion.
69. A method of operating one or more programmable electrical connections in an integrated circuit, the method comprising:
at least partially saturating a portion of one or more of the programmable electrical connections with a gas;
releasing gas at a first rate from the saturated portions of one or more of the programmable electrical connections;
in response to releasing gas at the first rate from the saturated portions of the one or more of the programmable electrical connections, changing electrical status of the one or more of the programmable electrical connections; and
releasing gas at a second rate different from the first rate from the saturated portions of one or more of the antifuses.
70. A method of operating one or more programmable electrical connections in an integrated circuit, the method comprising:
a step for at least partially saturating a portion of one or more of the programmable electrical connections with a gas;
a step for releasing gas at a first rate from the saturated portions of one or more of the programmable electrical connections;
a step for changing electrical status of the one or more of the programmable electrical connections, in response to initiation of the step for releasing gas at the first rate from the saturated portions of the one or more of the programmable electrical connections; and
a step for releasing gas at a second rate different from the first rate from the saturated

FOIEB0 "T6454550

portions of one or more of the antifuses to disarm the one or more of the antifuses.

71. A method of operating a programmable electrical connection in an integrated circuit, the method comprising:

applying a voltage to a resistor;

heating a hydride, oxide, nitride, or carbonate compound in response to applying the voltage to the resistor;

releasing or evolving a gas from the hydride, oxide, nitride, or carbonate compound in response to heating; and

moving a first conductive element relative a second conductive element in responsive to releasing or evolving the gas.

72. (New) A method of making an antifuse in an integrated-circuit assembly, the method comprising:

forming an opening in an insulative layer, with the opening exposing at least one conductor;

forming a metal layer in the opening;

forming a metal-oxide layer on the metal layer and within the opening,

forming a conductive layer on the metal-oxide layer and within the opening;

forming at least one conductive member on the insulative layer which overhangs the opening; and

saturating the metal layer with a gas comprises converting at least a portion of the metal layer into a metal hydride.

73. (New) A method of making an antifuse in an integrated-circuit assembly, the method comprising:

forming an opening in an insulative layer, with the opening exposing one or more conductors;

forming a metal layer in the opening, the metal layer consisting essentially of titanium, hafnium, niobium, tantalum, thorium, vanadium, or zirconium;

09/258,363

forming a metal-oxide layer on the metal layer and within the opening,
forming a conductive layer on the metal-oxide layer and within the opening; and
forming at least one conductive member on the insulative layer which overhangs the opening.

74. (New) The method of claim 73, wherein the conductive member on the insulative layer overhangs the opening by at least 250 angstroms.

75. (New) A method of making an antifuse in an integrated-circuit assembly, the method comprising:

forming an opening in an insulative layer, with the opening exposing one or more conductors;

forming a metal layer in the opening, the metal layer consisting essentially of titanium;

forming a metal-oxide layer on the metal layer and within the opening,

forming a conductive layer on the metal-oxide layer and within the opening; and

forming at least one conductive member on the insulative layer which overhangs the opening.

76. (New) The method of claim 75, wherein the conductive member on the insulative layer overhangs the opening by at least 250 angstroms.

77. (New) A method of making an antifuse in an integrated-circuit assembly, the method comprising:

forming an opening in an insulative layer, with the opening exposing one or more conductors;

forming a metal layer in the opening, the metal layer consisting essentially of hafnium;

forming a metal-oxide layer on the metal layer and within the opening,

forming a conductive layer on the metal-oxide layer and within the opening; and

forming at least one conductive member on the insulative layer which overhangs the opening.

FOOED "T6454650

78. (New) The method of claim 77, wherein the conductive member on the insulative layer overhangs the opening by at least 250 angstroms.
79. (New) A method of making an antifuse in an integrated-circuit assembly, the method comprising:
- forming an opening in an insulative layer, with the opening exposing one or more conductors;
 - forming a metal layer in the opening, the metal layer consisting essentially of niobium;
 - forming a metal-oxide layer on the metal layer and within the opening,
 - forming a conductive layer on the metal-oxide layer and within the opening; and
 - forming at least one conductive member on the insulative layer which overhangs the opening.
80. (New) The method of claim 79, wherein the conductive member on the insulative layer overhangs the opening by at least 250 angstroms.
81. (New) A method of making an antifuse in an integrated-circuit assembly, the method comprising:
- forming an opening in an insulative layer, with the opening exposing one or more conductors;
 - forming a metal layer in the opening, the metal layer consisting essentially of thorium;
 - forming a metal-oxide layer on the metal layer and within the opening,
 - forming a conductive layer on the metal-oxide layer and within the opening; and
 - forming at least one conductive member on the insulative layer which overhangs the opening.
82. (New) The method of claim 81, wherein the conductive member on the insulative layer overhangs the opening by at least 250 angstroms.
83. (New) A method of making an antifuse in an integrated-circuit assembly, the method

FILED "F045450"

comprising:

forming an opening in an insulative layer, with the opening exposing one or more
conductors;
forming a metal layer in the opening, the metal layer consisting essentially of vanadium;
forming a metal-oxide layer on the metal layer and within the opening,
forming a conductive layer on the metal-oxide layer and within the opening; and
forming at least one conductive member on the insulative layer which overhangs the
opening.

84. (New) The method of claim 83, wherein the conductive member on the insulative layer
overhangs the opening by at least 250 angstroms.

85. (New) A method of making an antifuse in an integrated-circuit assembly, the method
comprising:
forming an opening in an insulative layer, with the opening exposing one or more
conductors;
forming a metal layer in the opening, the metal layer consisting essentially of tantalum;
forming a metal-oxide layer on the metal layer and within the opening,
forming a conductive layer on the metal-oxide layer and within the opening; and
forming at least one conductive member on the insulative layer which overhangs the
opening.

86. (New) The method of claim 85, wherein the conductive member on the insulative layer
overhangs the opening by at least 250 angstroms.

87. (New) A method of making an antifuse in an integrated-circuit assembly, the method
comprising:
forming an opening in an insulative layer, with the opening exposing one or more
conductors;
forming a metal layer in the opening, the metal layer consisting essentially of zirconium;

09/258,363-0000

forming a metal-oxide layer on the metal layer and within the opening,
forming a conductive layer on the metal-oxide layer and within the opening; and
forming at least one conductive member on the insulative layer which overhangs the opening.

88. (New) The method of claim 87, wherein the conductive member on the insulative layer overhangs the opening by at least 250 angstroms.

89. (New) A method of making an antifuse in an integrated-circuit assembly, the method comprising:

forming an opening in an insulative layer, with the opening exposing one or more conductors;

forming a metal layer in the opening, the metal layer consisting essentially of titanium, hafnium, niobium, or tantalum;

forming a metal-oxide layer on the metal layer and within the opening,

forming a conductive layer on the metal-oxide layer and within the opening; and

forming at least one conductive member on the insulative layer which overhangs the opening.

90. (New) The method of claim 89, wherein the conductive member on the insulative layer overhangs the opening by at least 250 angstroms.

91. (New) A method of making an antifuse in an integrated-circuit assembly, the method comprising:

forming an opening in an insulative layer, with the opening exposing one or more conductors;

forming a metal layer in the opening, the metal layer consisting essentially of thorium, vanadium, or zirconium;

forming a metal-oxide layer on the metal layer and within the opening,

forming a conductive layer on the metal-oxide layer and within the opening; and

09/258,363-0001

forming at least one conductive member on the insulative layer which overhangs the opening.

92. (New) The method of claim 91, wherein the conductive member on the insulative layer overhangs the opening by at least 250 angstroms.

93. (New) A method of making an antifuse in an integrated-circuit assembly, the method comprising:

forming an opening in an insulative layer, with the opening exposing one or more conductors;

forming a metal layer in the opening, the metal layer consisting essentially of titanium, hafnium, niobium, tantalum, thorium, vanadium, or zirconium;

forming a metal-oxide layer on the metal layer and within the opening,

forming a conductive layer on the metal-oxide layer and within the opening, the conductive layer comprising more than trace quantities of aluminum, gold, silver, and/or copper; and

forming at least one conductive member on the insulative layer which overhangs the opening.

94. (New) The method of claim 93, wherein the conductive member on the insulative layer overhangs the opening by at least 250 angstroms.

09/258,363